**Project Title**: Lower Cost 1.2kV Foundry Process for SiC Planar Gate Power MOSFETs and JBS Rectifiers

**Objectives**: Reduce manufacturing cost for SiC MOSFETs and JBS Rectifiers

**Major Milestones**: Fabrication of 3 Process Qual Lots

**Deliverables**: Statistical Data and Wafer Maps

**WBG Technology Impact**

1. Open domain manufacturing process for 1.2kV SiC MOSFETs and JBS rectifiers
2. Market segments impacted: EV/HEV inverter, PV Inverter, SMPS, etc
3. Timeframe for commercialization: BP-3
4. The outcome of this project will serve as the baseline process for PA members to design their own products and manufacture them at X-Fab.

**More WBG Impact and Additional impacts**

1. Increase market penetration for SiC power MOSFETs.
2. Workforce Development: 1 graduate student and two undergraduate students are involved.
3. TRL level
   - At project start: TRL7
   - Expected at project completion: TRL8